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**MAY 31 2002**

**Application Number**  
**10/056,611**

**Applicant(s)**

Shiro SAKAI

Filing Date

**January 24, 2002**

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U.S. PATENT DOCUMENTS

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## FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO
TA	B1	11-266004	09/28/1999	Japan	H01L	29/06		✓
	B2	9-227298	09/02/1997	Japan	C30B	29/38		✓
	B3	10-22568	01/23/1998	Japan	H01S	3/18		✓
	B4	11-135832	05/21/1999	Japan	H01L	33/00		✓
TN	B5	11-145057	05/28/1999	Japan	H01L	21/20		✓

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IN	B6	Patent Abstract of Japanese Patent No. JP10312971, published 11/24/1998, 1 page
IN	B7	Patent Abstract of Japanese Patent No. JP2000021789, published 01/21/2000, 1 page

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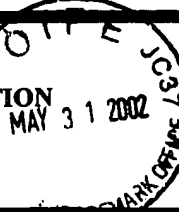
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**SHEET 3                      OF 7**

**INFORMATION DISCLOSURE CITATION**  
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Docket Number (Optional)  
08228/020001

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**FOREIGN PATENT DOCUMENTS**

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							YES	NO
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	D2	4-297023	10/21/1992	Japan	H01L	21/205		✓
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<i>EW</i>	D4	Patent Abstract of Japanese Patent No. JP11354842, published 12/24/1999, 1 page
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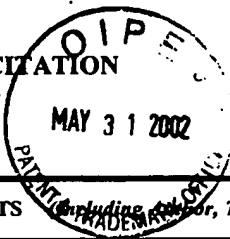
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Group Art Unit  
2812

*EXAMINER INITIAL	OTHER DOCUMENTS (Including Abstracts, Title, Date, Pertinent Pages, Etc.)	COPY OF PAPERS ORIGINAL Y FILED
TV	F1 Patent Abstracts of Japan, Publication No. 11135832A, published 05/21/1999, 1 page	
	F2 Patent Abstracts of Japan, Publication No. 11145057A, published 05/28/1999, 1 page	
	F3 Patent Abstracts of Japan, Publication No. 11145516A, published 05/28/1999, 1 page	
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	F5 Patent Abstracts of Japan, Publication No. 11346035A, published 12/14/1999, 1 page	
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Group A-1 Unit 1

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08228/02000

**10/056,611**

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2813

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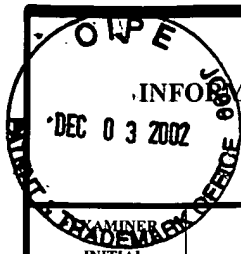
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## INFORMATION DISCLOSURE CITATION

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Docket Number (Optional)

08228.0200

Application Number

10/056,611

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Shiro SAKAI

Filing Date

01/24/2002

Group Art Unit

2813

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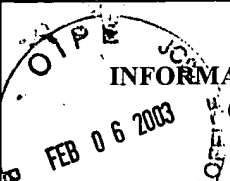
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	Applicant(s) <b>Shiro SAKAI</b>	
	Filing Date <b>01/24/2002</b>	Group Art Unit <b>2813</b>

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*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
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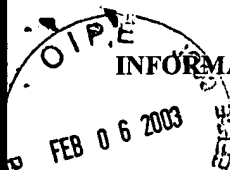
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
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TA	B1	EP 0 180 222 A2	05/07/1986	EPO	H01L	31/18		
I	B2	EP 0 180 222 A3	05/07/1986	EPO	H01L	21/308		
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EXAMINER 	DATE CONSIDERED <b>3/19/02</b>
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	Applicant(s) <b>Shiro SAKAI</b>	
	Filing Date <b>01/24/2002</b>	Group Art Unit <b>2813</b>

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**FOREIGN PATENT DOCUMENTS**

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**OTHER DOCUMENTS** (Including Author, Title, Date, Pertinent Pages, Etc.)

<i>th</i>	C3	European Search Report dated 01/08/2003, 3 pages

EXAMINER <i>[Signature]</i>	DATE CONSIDERED <i>3/19/03</i>
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